ST2301D

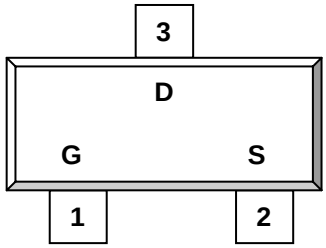
P Channel Enhancement Mode MOSFET

-2.0A

DESCRIPTION

The ST2301D is the P-Channel logic enhancement mode power field effect transistor is produced using high cell density, DMOS trench technology.
This high density process is especially tailored to minimize on-state resistance.
These devices are particularly suited for low voltage application such as cellular phone and notebook computer power management and other batter powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

PIN CONFIGURATION
SOT-23

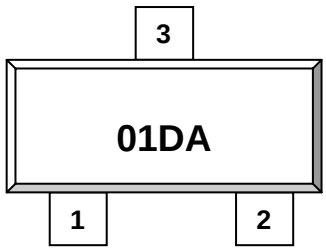


1.Gate 2.Source 3.Drain

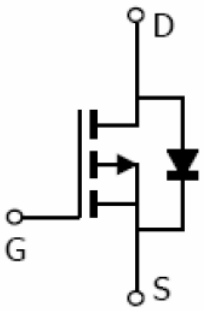
FEATURE

- -20V/-2.0A, $R_{DS(ON)}$ = 180m-ohm (Typ.) @V_{GS} = -4.5V
- -20V/-1.5A, $R_{DS(ON)}$ = 360m-ohm @V_{GS} = -2.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOT-23 package design

PART MARKING
SOT-23



D; Product Code A: Process Code



ORDERING INFORMATION

Part Number	Package	Part Marking
ST2301DSRG	SOT-23	01DA

※ Process Code : A ~ Z ; a ~ z
※ ST2301DSRG S : SOT-23 ; R : Tape Reel ; G : Pb – Free

120 Bentley Square, Mountain View, Ca 94040 USA
www.stansontech.com

ABSOULTE MAXIMUM RATINGS (Ta = 25℃ Unless otherwise noted)

Parameter		Symbol	Typical	Unit
Drain-Source Voltage		V_{DSS}	-20	V
Gate-Source Voltage		V_{GSS}	±12	V
Continuous Drain CurrentTJ=150℃)	T_A=25℃ T_A=70℃	I_D	-2.0 -1.2	A
Pulsed Drain Current		I_{DM}	-6.0	A
Continuous Source Current (Diode Conduction)		I_S	-1.6	A
Power Dissipation	T_A=25℃ T_A=70℃	P_D	1.25 0.8	W
Operation Junction Temperature		T_J	150	℃
Storgae Temperature Range		T_{STG}	-55/150	℃
Thermal Resistance-Junction to Ambient		$R_{\theta JA}$	105	℃/W

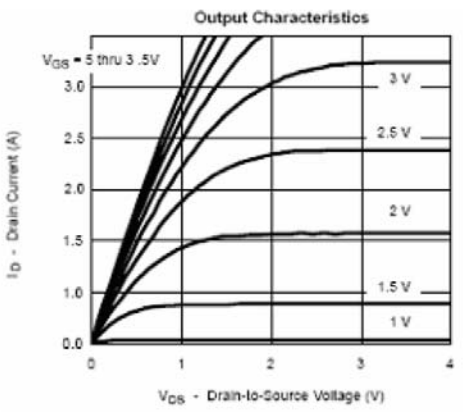
120 Bentley Square, Mountain View, Ca 94040 USA
www.stansontech.com

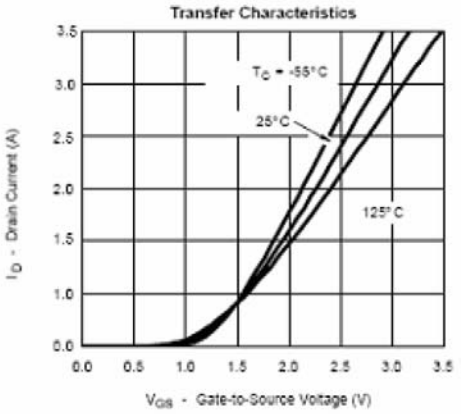
ELECTRICAL CHARACTERISTICS (Ta = 25℃ Unless otherwise noted)

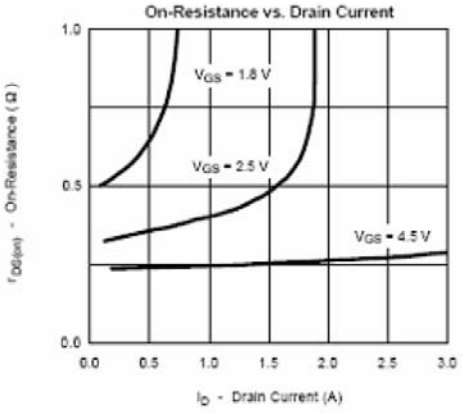
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS}=0V,I_D=-250uA	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=VGS,I_D=-250uA	-0.3		-1.0	V
Gate Leakage Current	I_{GSS}	V_{DS}=0V,V_{GS}=±12V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-20V,V_{GS}=0V			-1	uA
		V_{DS}=-20V,V_{GS}=0V T_J=55℃			-5	
On-State Drain Current	$I_{D(on)}$	V_{DS}≦-4.5V,V_{GS}=-5V	-2.0			A
Drain-source On-Resistance	$R_{DS(on)}$	V_{GS}=-4.5V,I_D=-2.0A V_{GS}=-2.5V,I_D=-1.5A		0.180 0.360		Ω
Forward Transconductance	g_{fs}	V_{DS}=-5V,I_D=-2.8V		0.5		S
Diode Forward Voltage	V_{SD}	I_S=-1.6A,V_{GS}=0V		-0.8	-1.2	V
Dynamic						
Total Gate Charge	Q_g	V_{DS}=-10V V_{GS}=-4.5V I_D≡-0.7A		1.5	2.0	nC
Gate-Source Charge	Q_{gs}			0.3		
Gate-Drain Charge	Q_{gd}			0.35		
Turn-On Time	$t_{d(on)}$ tr	V_{DD}=-10V R_L=10Ω I_D=-1.0A V_{GEN}=-4.5V R_G=6Ω		5	10	nS
				15	25	
Turn-Off Time	$t_{d(off)}$ tf			8	15	
				1.4	1.8	

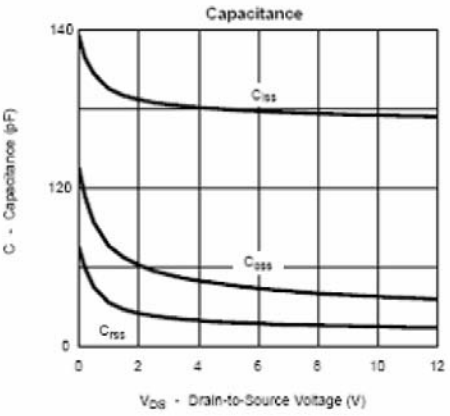
120 Bentley Square, Mountain View, Ca 94040 USA
www.stansontech.com

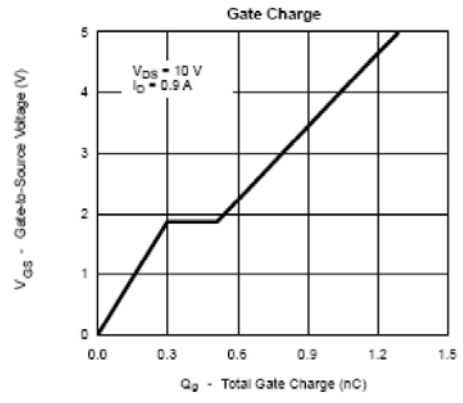
TYPICAL CHARACTERICTICS (25℃ Unless noted)

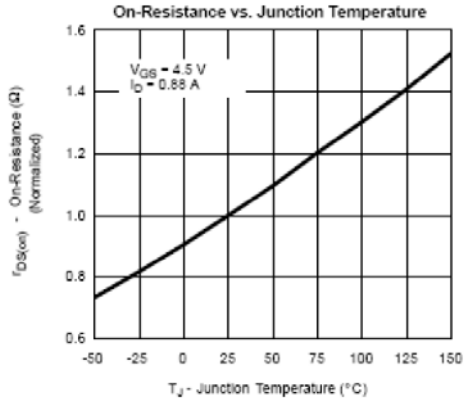




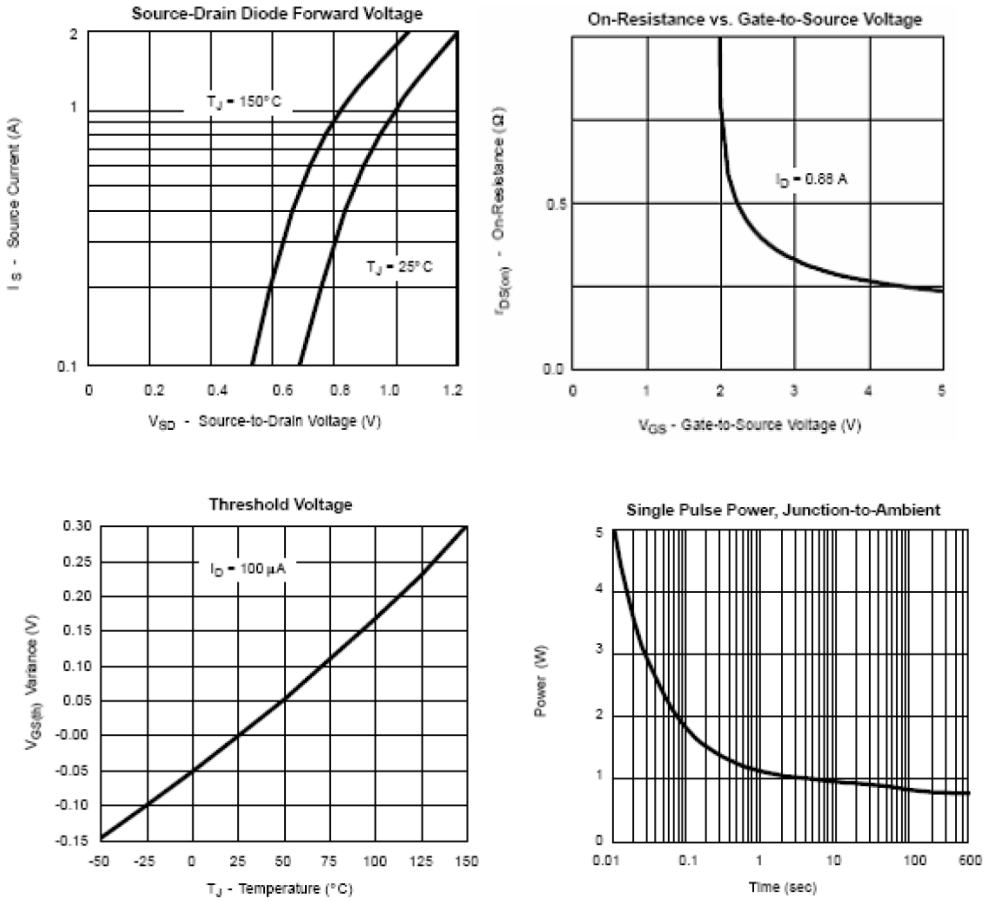






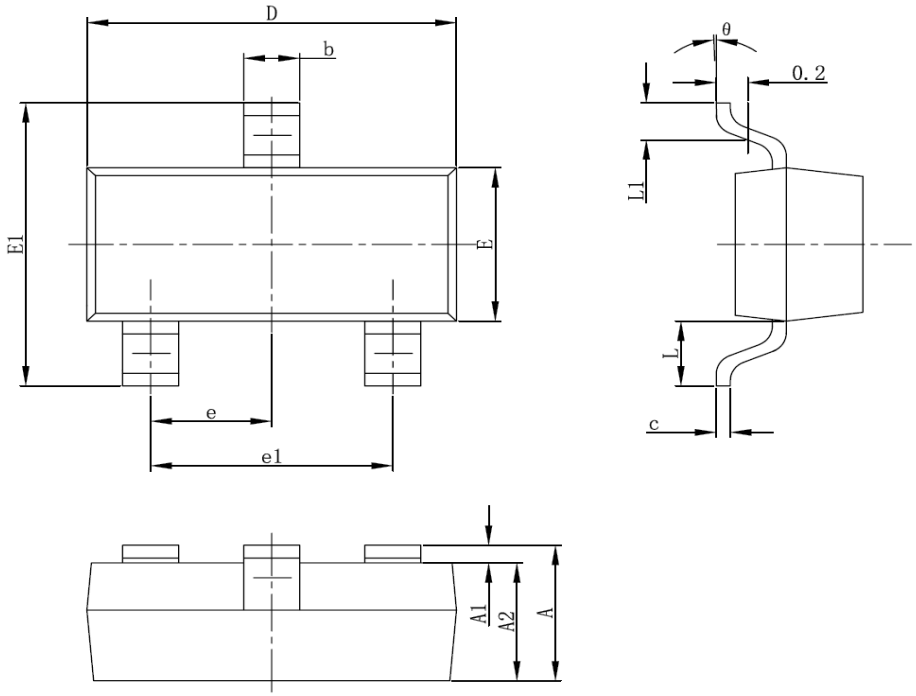


TYPICAL CHARACTERICTICS (25℃ Unless noted)



120 Bentley Square, Mountain View, Ca 94040 USA
www.stansontech.com

SOT-23 PACKAGE OUTLINE



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

120 Bentley Square, Mountain View, Ca 94040 USA
www.stansontech.com